# 8-Bit Shift Register with Output Storage Register (3-State)

The MC74VHC595 is an advanced high speed 8-bit shift register with an output storage register fabricated with silicon gate CMOS technology.

It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC595 contains an 8-bit static shift register which feeds an 8-bit storage register.

Shift operation is accomplished on the positive going transition of the Shift Clock input (SCK). The output register is loaded with the contents of the shift register on the positive going transition of the Register Clock input (RCK). Since the RCK and SCK signals are independent, parallel outputs can be held stable during the shift operation. And, since the parallel outputs are 3-state, the VHC595 can be directly connected to an 8-bit bus. This register can be used in serial-to-parallel conversion, data receivers, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

# **Features**

- High Speed:  $f_{max} = 185MHz$  (Typ) at  $V_{CC} = 5V$
- Low Power Dissipation:  $I_{CC} = 4\mu A$  (Max) at  $T_A = 25^{\circ}C$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise: V<sub>OLP</sub> = 1.0V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V
- These are Pb-Free Devices



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### MARKING DIAGRAMS

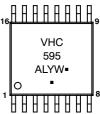


SOIC-16 D SUFFIX CASE 751B



TSSOP-16 DT SUFFIX CASE 948F





A = Assembly Location

WL = Wafer Lot Y = Year W, WW = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

# **PIN ASSIGNMENT**

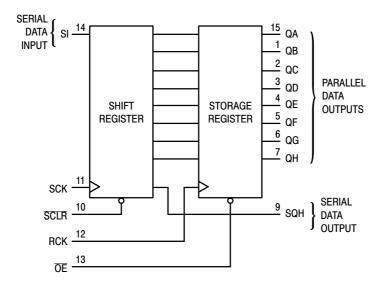
QB	
QD 3 14 SI	
Т Г	
QE [] 4 13 ] OE	
QF [ 5 12 ] RCK	
QG [ 6 11 ] SCK	
QH 7 10 SCL	7
GND [ 8 9 ] SQH	

# **ORDERING INFORMATION**

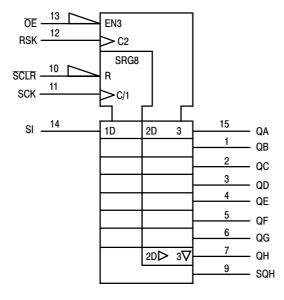
Device	Package	Shipping <sup>†</sup>
MC74VHC595DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74VHC595DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

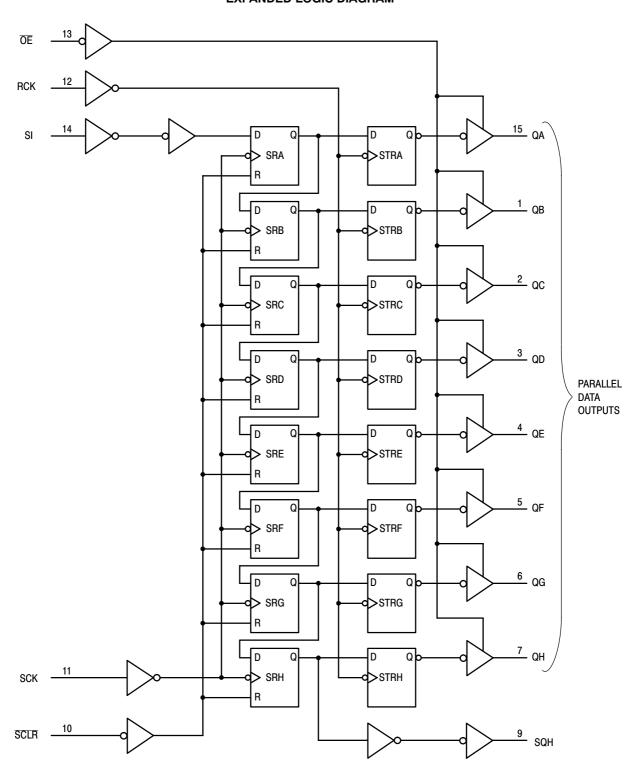
# **LOGIC DIAGRAM**



# **IEC LOGIC SYMBOL**



# **EXPANDED LOGIC DIAGRAM**



### **FUNCTION TABLE**

			Inputs				Resulting F	unction	
Operation	Reset (SCLR)	Serial Input (SI)	Shift Clock (SCK)	Reg Clock (RCK)	Output Enable (OE)	Shift Register Contents	Storage Register Contents	Serial Output (SQH)	Parallel Outputs (QA - QH)
Clear shift register	L	Х	Х	L, H, ↓	L	L	U	L	U
Shift data into shift register	Н	D	1	L, H, ↓	L	$\begin{array}{c} \text{D}{\rightarrow}\text{SR}_{\text{A}};\\ \text{SR}_{\text{N}}{\rightarrow}\text{SR}_{\text{N+1}} \end{array}$	U	SR <sub>G</sub> →SR <sub>H</sub>	U
Registers remains unchanged	Н	Х	L, H, ↓	Х	L	U	**	U	**
Transfer shift register contents to storage register	Н	Х	L, H, ↓	1	L	U	SR <sub>N</sub> →STR <sub>N</sub>	*	SR <sub>N</sub>
Storage register remains unchanged	Х	Х	Х	L, H, ↓	L	*	U	*	U
Enable parallel outputs	Х	Х	Х	Х	L	*	**	*	Enabled
Force outputs into high impedance state	Х	Х	Х	Х	Н	*	**	*	Z

SR = shift register contents

 $\downarrow$  = High-to-Low

\* = depends on Reset and Shift Clock

STR = storage register contents U = remains unchanged

↑ = Low-to-High

### **MAXIMUM RATINGS\***

Symbol	Paramete	r	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage		- 0.5 to + 7.0	V
V <sub>out</sub>	DC Output Voltage		$-0.5$ to $V_{CC} + 0.5$	V
I <sub>IK</sub>	Input Diode Current		- 20	mA
I <sub>OK</sub>	Output Diode Current		± 20	mA
l <sub>out</sub>	DC Output Current, per Pin		± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and G	ND Pins	± 50	mA
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature		- 65 to + 150	°C

Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

†Derating — SOIC Packages: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

# RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage		2.0	5.5	V
V <sub>in</sub>	DC Input Voltage		0	5.5	V
V <sub>out</sub>	DC Output Voltage		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Ty	pes	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time V	$_{CC} = 3.3V \pm 0.3V$ $_{CC} = 5.0V \pm 0.5V$	0 0	100 20	ns/V

D = data (L, H) logic level

inputs

<sup>\*\* =</sup> depends on Register Clock input

The  $\theta_{JA}$  of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

# DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

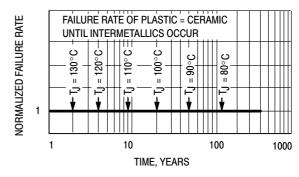


Figure 1. Failure Rate vs. Time Junction Temperature

### DC ELECTRICAL CHARACTERISTICS

			v <sub>cc</sub>		T <sub>A</sub> = 25°C	;	<b>T</b> <sub>A</sub> = ≤	≤ 85°C	<b>T</b> <sub>A</sub> = ≤	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.59 0.9 1.35 1.65		0.59 0.9 1.35 1.65		0.59 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Maximum Low-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 4$ mA $I_{OL} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μΑ
Icc	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0		40.0	μА
I <sub>OZ</sub>	Three-State Output Off-State Current	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or }$ GND	5.5			± 0.25		± 2.5		± 2.5	μА

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$ )

					T <sub>A</sub> = 25°C	;	T <sub>A</sub> = 5	≤ 85°C	<b>T</b> <sub>A</sub> = ≤	125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
f <sub>max</sub>	Maximum Clock Frequency (50%	$V_{CC} = 3.3 \pm 0.3 \text{ V}$		80	150		70		70		MHz
	Duty Cycle)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$		135	185		115		115		
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, SCK to	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		8.8 11.3	13.0 16.5	1.0 1.0	15.0 18.5	1.0 1.0	15.0 18.5	ns
	SQH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		6.2 7.7	8.2 10.2	1.0 1.0	9.4 11.4	1.0 1.0	9.4 11.4	
t <sub>PHL</sub>	Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		8.4 10.9	12.8 16.3	1.0 1.0	13.7 17.2	1.0 1.0	13.7 17.2	ns
	CPLR to SQH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		5.9 7.4	8.0 10.0	1.0 1.0	9.1 11.1	1.0 1.0	9.1 11.1	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, RCK to	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		7.7 10.2	11.9 15.4	1.0 1.0	13.5 17.0	1.0 1.0	13.5 17.0	ns
	QA-QH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		5.4 6.9	74 9.4	1.0 1.0	8.5 10.5	1.0 1.0	8.5 10.5	
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15pF$ $C_L = 50pF$		7.5 9.0	11.5 15.0	1.0 1.0	13.5 17.0	1.0 1.0	13.5 17.0	ns
	OE to QA-QH	$V_{CC}$ = 5.0 $\pm$ 0.5 $V$ R <sub>L</sub> = 1 k $\Omega$	$C_L = 15pF$ $C_L = 50pF$		4.8 8.3	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	10.0 12.0	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time,	$V_{CC}$ = 3.3 $\pm$ 0.3 $V$ R <sub>L</sub> = 1 k $\Omega$	C <sub>L</sub> = 50pF		12.1	15.7	1.0	16.2	1.0	16.2	ns
	OE to QA-QH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 50pF		7.6	10.3	1.0	11.0	1.0	11.0	
C <sub>IN</sub>	Input Capacitance				4	10		10		10	pF
C <sub>OUT</sub>	Three-State Output Capacitance (Output in High-Impedance State), QA-QH				6			10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0V	
$C_{PD}$	Power Dissipation Capacitance (Note 1)	87	pF

C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		$T_A =$	25°C	
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.8	1.0	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	- 0.8	- 1.0	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V

# **TIMING REQUIREMENTS** (Input $t_r = t_f = 3.0 \text{ns}$ )

		V <sub>cc</sub>	T <sub>A</sub> =	T <sub>A</sub> = 25°C		T <sub>A</sub> = - 55 to 125°C		
Symbol	Parameter	v	Тур	Limit	Limit	Limit	Unit	
t <sub>su</sub>	Setup Time, SI to SCK	3.3 5.0		3.5 3.0	3.5 3.0	3.5 3.0	ns	
t <sub>su(H)</sub>	Setup Time, SCK to RCK	3.3 5.0		8.0 5.0	8.5 5.0	8.5 5.0	ns	
t <sub>su(L)</sub>	Setup Time, SCLR to RCK	3.3 5.0		8.0 5.0	9.0 5.0	9.0 5.0	ns	
t <sub>h</sub>	Hold Time, SI to SCK	3.3 5.0		1.5 2.0	1.5 2.0	1.5 2.0	ns	
t <sub>h(L)</sub>	Hold Time, SCLR to RCK	3.3 5.0		0	0	1.0 1.0	ns	
t <sub>rec</sub>	Recovery Time, SCLR to SCK	3.3 5.0		3.0 2.5	3.0 2.5	3.0 2.5	ns	
t <sub>w</sub>	Pulse Width, SCK or RCK	3.3 5.0		5.0 5.0	5.0 5.0	5.0 5.0	ns	
t <sub>w(L)</sub>	Pulse Width, SCLR	3.3 5.0		5.0 5.0	5.0 5.0	5.0 5.0	ns	

### **SWITCHING WAVEFORMS**

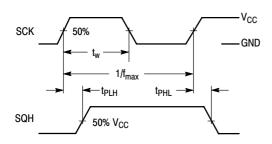


Figure 2.

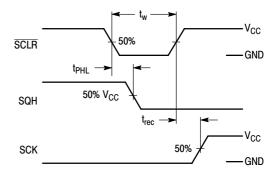


Figure 3.

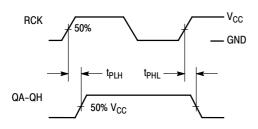


Figure 4.

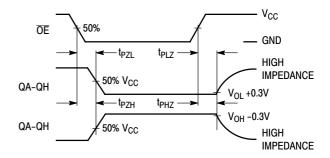


Figure 5.

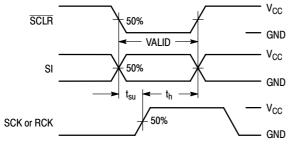


Figure 6.

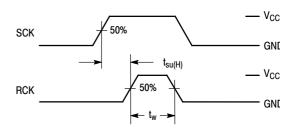
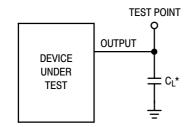


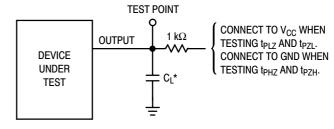
Figure 7.

# **TEST CIRCUITS**



\*Includes all probe and jig capacitance

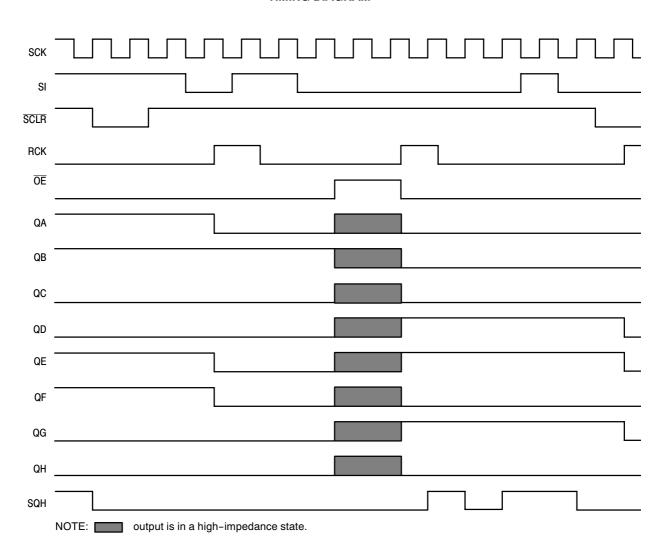
Figure 8.



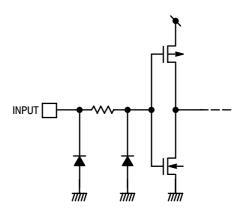
\*Includes all probe and jig capacitance

Figure 9.

# **TIMING DIAGRAM**

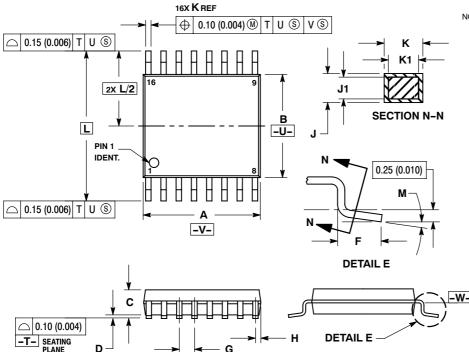


# **INPUT EQUIVALENT CIRCUIT**



### PACKAGE DIMENSIONS

# TSSOP-16 CASE 948F-01 **ISSUE B**



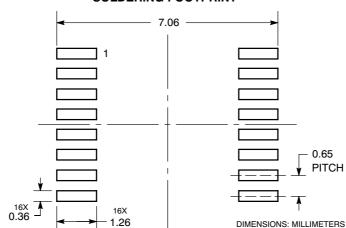
- JIES:

  1. DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION S NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
ſ	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	6.40 BSC 0.252 BSC			
М	0°	8°	0°	8 °	

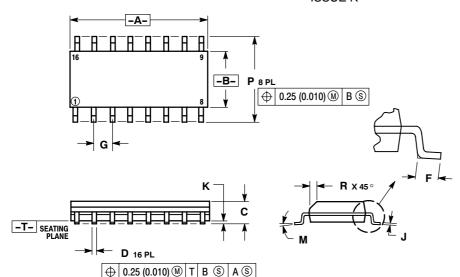
# **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### PACKAGE DIMENSIONS

# SOIC-16 CASE 751B-05 ISSUE K

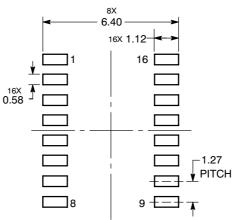


### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
   DIMENSIONS A AND B DO NOT INCLUDE MOLD
- DIMENSIONS A AND B DO NOT INCLUDE MOLI PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALLB E 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

# **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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